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# NTE643
# Silicon Dual Schottky Rectifier
# 200V, 10 Amp, TO220 Type Package

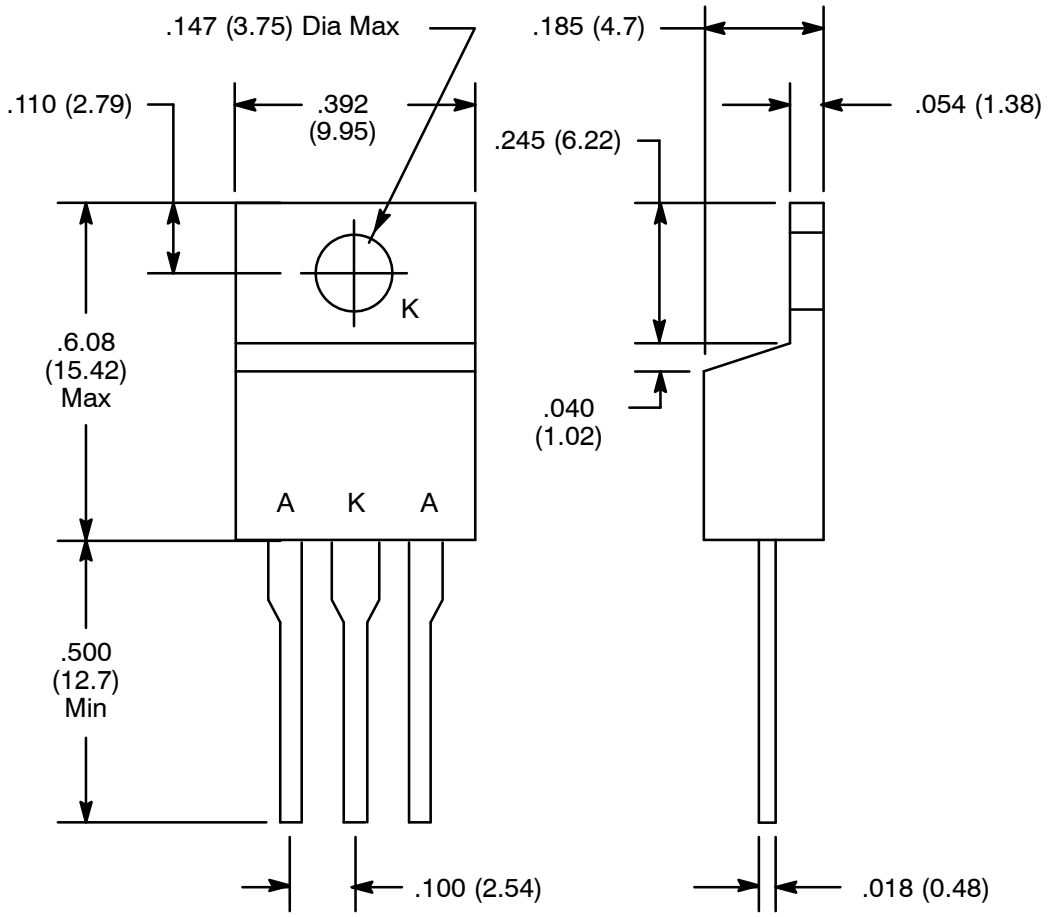
**Features:**

- Schottky Barrier Chip
- Guard Ring for Transient Protection
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Surge Current capability

**Maximum Ratings and Electrical Characteristics:** ($T_A$ = +25°C unless otherwise specified. Single Phase, Half Wave, 60Hz, Resistive or Inductive load. For capacitive load, derate current by 20%)

Peak Repetitive Reverse Voltage, $V_{RRM}$ . . . . . 200V
Working Peak Reverse Voltage, $V_{RWM}$ . . . . . 200V
DC Blocking Voltage, $V_R$ . . . . . 200V
RMS Reverse Voltage, $V_{R(RMS)}$ . . . . . 140V
Average Rectified Output Current ($T_C$ = +95°C), $I_O$ . . . . . 10A
Non–Repetitive Peak Forward Surge Current, $I_{FSM}$
(8.3ms Single Half Sine–Wave Superimposed on Rated Load) . . . . . 150A
Forward Voltage ($I_F$ = 5A), $V_{FM}$ . . . . . 0.92V
Peak Reverse Current (At Rated DC Blocking Voltage), $I_{RM}$
$T_A$ = +25°C . . . . . 0.5mA
$T_A$ = +100°C . . . . . 50mA
Typical Junction Capacitance (Note 1), $C_j$ . . . . . 700pF
Operating Junction Temperature Range, $T_J$ . . . . . –65° to +150°C
Storage Temperature Range, $T_{stg}$ . . . . . –65° to +150°C

Note 1. Measured at 1MHz and applied reverse voltage of 4VDC.


.147 (3.75) Dia Max
.185 (4.7)
.110 (2.79)
.392
(9.95)
.054 (1.38)
.245 (6.22)
K
.6.08
(15.42)
Max
.040
(1.02)
A K A
.500
(12.7)
Min
.100 (2.54)
.018 (0.48)